STARPOWER

SEMICONDUCTOR **IGBT**

GD150HFY120C1S

1200V/150A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

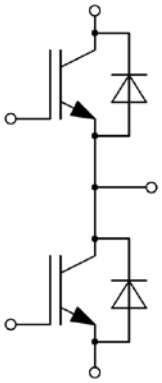
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 10μs short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings T_C=25°C unless otherwise noted

IGBT

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	±20	V
I_C	Collector Current @ T_C=25°C @ T_C=100°C	230 150	A
I_{CM}	Pulsed Collector Current t_p=1ms	300	A
P_D	Maximum Power Dissipation @ T_j=175°C	746	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	150	A
I_{FM}	Diode Maximum Forward Current t_p=1ms	300	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	°C
T_{jop}	Operating Junction Temperature	-40 to +150	°C
T_{STG}	Storage Temperature Range	-40 to +125	°C
V_{ISO}	Isolation Voltage RMS,f=50Hz,t=1min	4000	V

IGBT Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C=150A,V_{GE}=15V, T_j=25°C		1.65	2.10	V
		I_C=150A,V_{GE}=15V, T_j=125°C		1.95		
		I_C=150A,V_{GE}=15V, T_j=150°C		2.00		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	I_C=3.75mA,V_{CE}=V_{GE}, T_j=25°C	5.2	6.0	6.8	V
I_{CES}	Collector Cut-Off Current	V_{CE}=V_{CES},V_{GE}=0V, T_j=25°C			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE}=V_{GES},V_{CE}=0V, T_j=25°C			400	nA
R_{Gint}	Internal Gate Resistance			2.0		Ω
C_{ies}	Input Capacitance	V_{CE}=30V,f=1MHz, V_{GE}=0V		13.0		nF
C_{res}	Reverse Transfer Capacitance			0.42		nF
Q_G	Gate Charge	V_{GE}=-15…+15V		0.82		μC
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=150A, R_G=1.0Ω,V_{GE}=±15V, T_j=25°C		292		ns
t_r	Rise Time			59		ns
$t_{d(off)}$	Turn-Off Delay Time			344		ns
t_f	Fall Time			191		ns
E_{on}	Turn-On Switching Loss			4.55		mJ
E_{off}	Turn-Off Switching Loss			11.6		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=150A, R_G=1.0Ω,V_{GE}=±15V, T_j=125°C		297		ns
t_r	Rise Time			65		ns
$t_{d(off)}$	Turn-Off Delay Time			370		ns
t_f	Fall Time			315		ns
E_{on}	Turn-On Switching Loss			6.85		mJ
E_{off}	Turn-Off Switching Loss			16.1		mJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC}=600V,I_C=150A, R_G=1.0Ω,V_{GE}=±15V, T_j=150°C		288		ns
t_r	Rise Time			65		ns
$t_{d(off)}$	Turn-Off Delay Time			373		ns
t_f	Fall Time			342		ns
E_{on}	Turn-On Switching Loss			7.45		mJ
E_{off}	Turn-Off Switching Loss			18.8		mJ
I_{SC}	SC Data	t_P≤10μs,V_{GE}=15V, T_j=150°C,V_{CC}=900V, V_{CEM}≤1200V		600		A

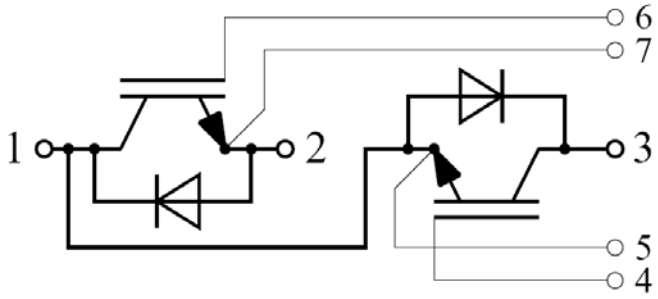
Diode Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	I_F=150A,V_{GE}=0V,T_j=25°C		1.65	2.05	V
		I_F=150A,V_{GE}=0V,T_j=125°C		1.65		
		I_F=150A,V_{GE}=0V,T_j=150°C		1.65		
Q_r	Recovered Charge	V_R=600V,I_F=150A, -di/dt=2700A/μs,V_{GE}=-15V T_j=25°C		17.0		μC
I_{RM}	Peak Reverse Recovery Current			140		A
E_{rec}	Reverse Recovery Energy			9.75		mJ
Q_r	Recovered Charge	V_R=600V,I_F=150A, -di/dt=2700A/μs,V_{GE}=-15V T_j=125°C		27.8		μC
I_{RM}	Peak Reverse Recovery Current			175		A
E_{rec}	Reverse Recovery Energy			14.9		mJ
Q_r	Recovered Charge	V_R=600V,I_F=150A, -di/dt=2700A/μs,V_{GE}=-15V T_j=150°C		31.8		μC
I_{RM}	Peak Reverse Recovery Current			184		A
E_{rec}	Reverse Recovery Energy			17.0		mJ

Module Characteristics T_C=25°C unless otherwise noted

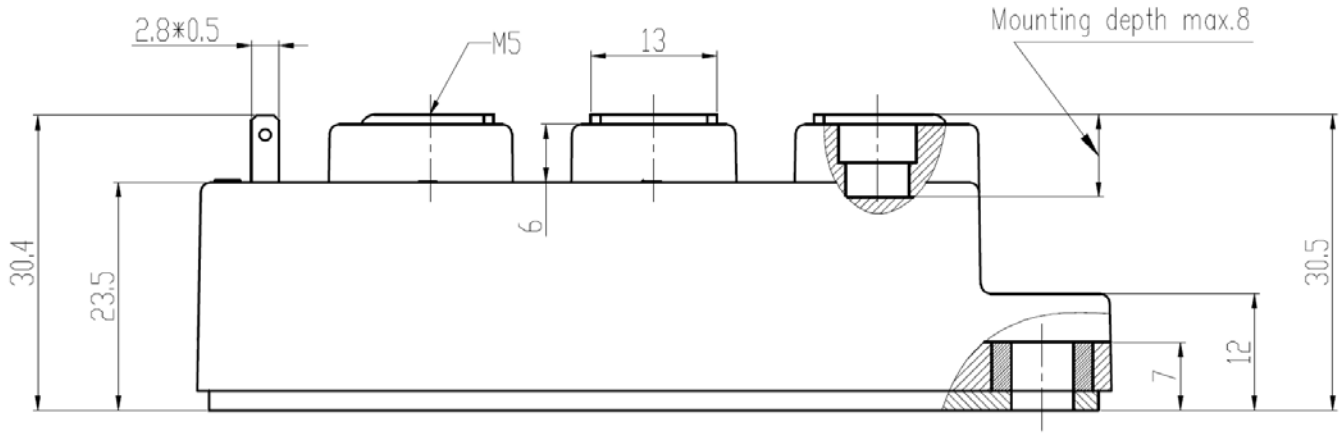
Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			30	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.75		mΩ
$R_{\theta JC}$	Junction-to-Case (per IGBT) Junction-to-Case (per Diode)			0.201 0.326	K/W
$R_{\theta CS}$	Case-to-Sink (per IGBT) Case-to-Sink (per Diode)		0.162 0.262		K/W
$R_{\theta CS}$	Case-to-Sink		0.05		K/W
M	Terminal Connection Torque, Screw M5 Mounting Torque, Screw M6	2.5 3.0		5.0 5.0	N.m
G	Weight of Module		150		g

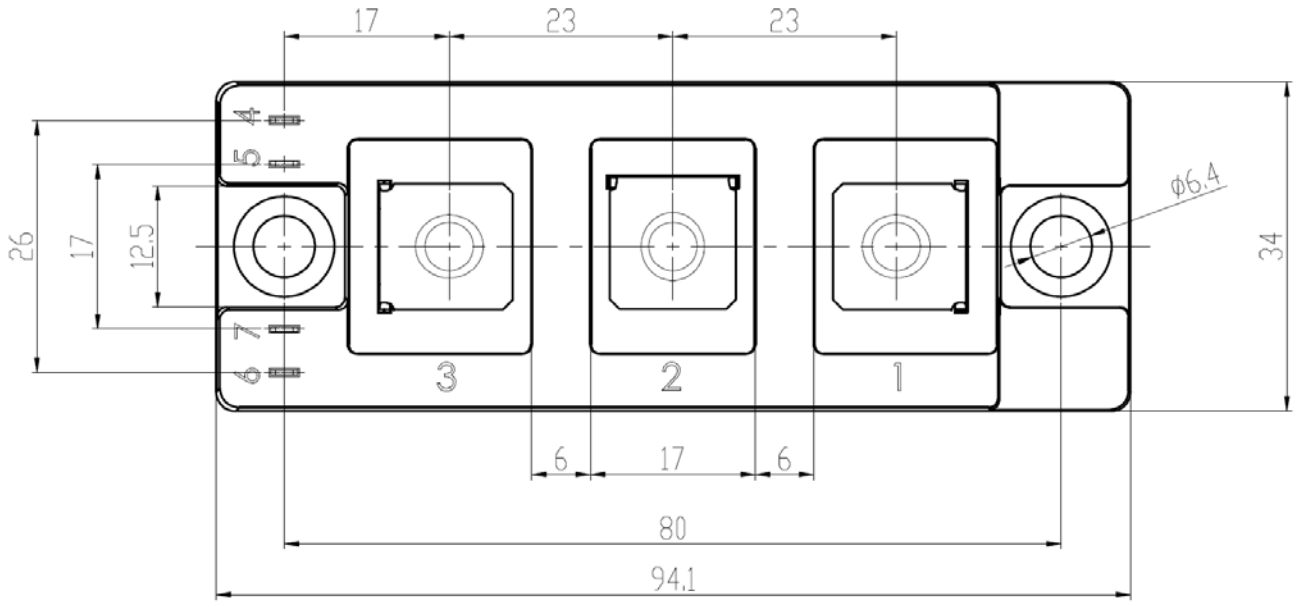
Circuit Schematic



Package Dimensions

Dimensions in Millimeters





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